

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	4	(plasma adj3 etching) same (low adj3 K adj3 dielectric) same (residue or residues)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/08 18:36
2	BRS	L2	103	(ash or ashing or ashed) adj10 (wafer or wafers or substrate or substrates) same photoresist same (residue or residues)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/08 18:38
3	BRS	L3	2	2 and (brush or brushes or brushing)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/08 18:39

438/906, 710,

FOR 389

430/317, 331, 134, 1.3

438/626, 633, 638